

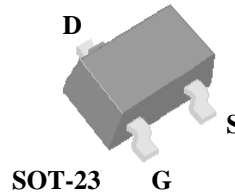
# XP10TN135N

**Halogen-Free Product**



*N-CHANNEL ENHANCEMENT MODE  
POWER MOSFET*

- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ Low Gate Charge
- ▼ RoHS Compliant & Halogen-Free

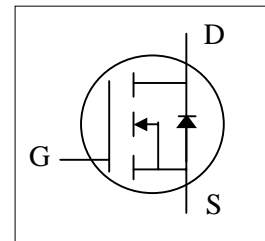


$BV_{DSS}$	100V
$R_{DS(ON)}$	135m $\Omega$
$I_D$	3A

## Description

XP10TN135 series are innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The special design SOT-23 package with good thermal performance is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.



## Absolute Maximum Ratings@ $T_J=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ\text{C}$	Drain Current, $V_{GS}$ @ 10V	3	A
$I_D@T_A=25^\circ\text{C}$	Drain Current, $V_{GS}$ @ 10V <sup>3</sup>	2.1	A
$I_D@T_A=70^\circ\text{C}$	Drain Current, $V_{GS}$ @ 10V <sup>3</sup>	1.7	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	10	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	1.38	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	45	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	90	$^\circ\text{C}/\text{W}$

**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =2A	-	112	135	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A	-	120	145	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.7	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =2A	-	8	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V	-	-	25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =2A	-	12	20	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =80V	-	2.2	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =10V	-	2.5	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =50V	-	7	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	5	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	16	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =10V	-	6	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	610	980	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	40	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	25	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	2.2	4.4	Ω

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =1.2A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =2A, V <sub>GS</sub> =0V,	-	21	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	21	-	nC

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board, t ≤10sec ; 270 °C/W when mounted on Min. copper pad.

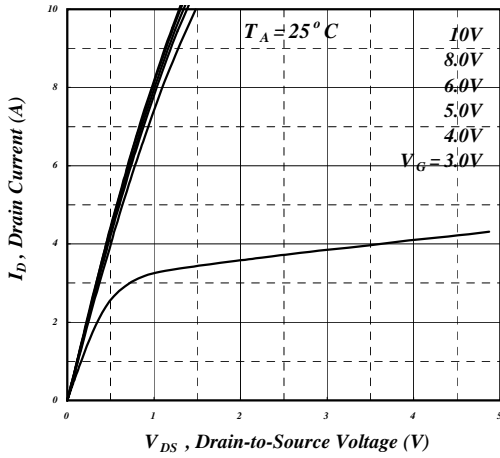
THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

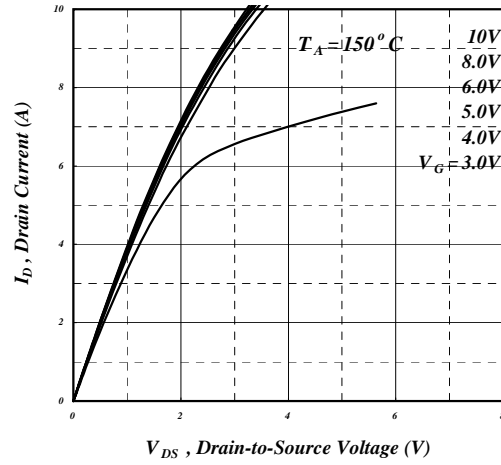
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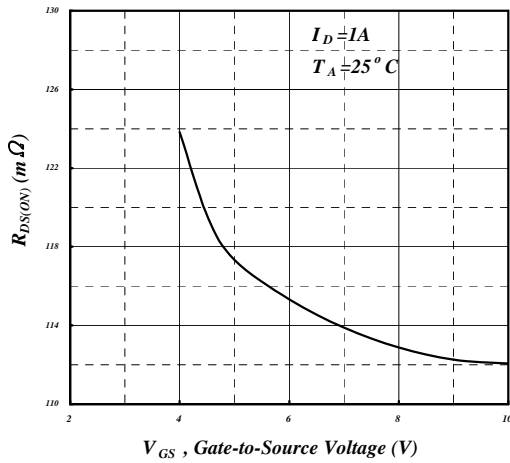
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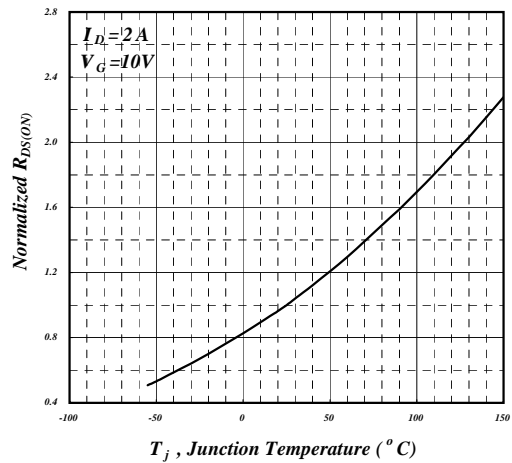
**Fig 1. Typical Output Characteristics**



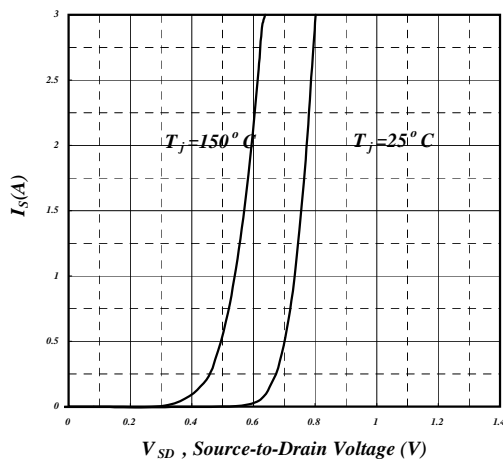
**Fig 2. Typical Output Characteristics**



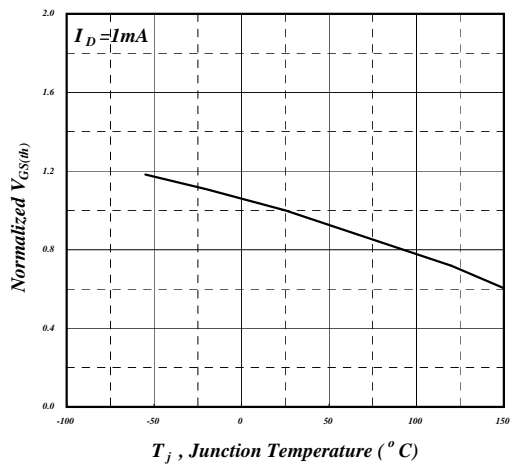
**Fig 3. On-Resistance v.s. Gate Voltage**



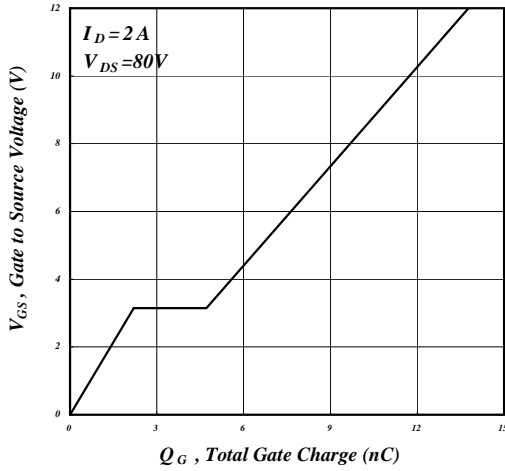
**Fig 4. Normalized On-Resistance v.s. Junction Temperature**



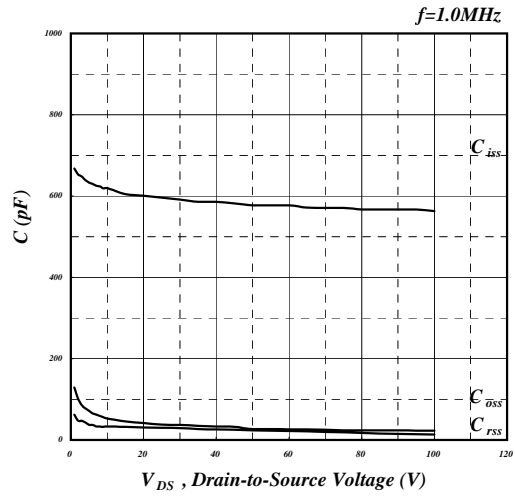
**Fig 5. Forward Characteristic of Reverse Diode**



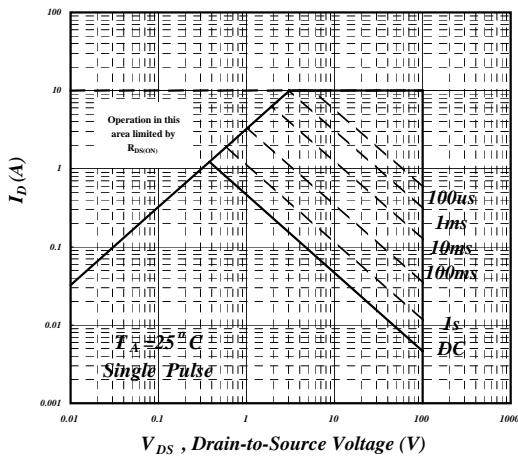
**Fig 6. Gate Threshold Voltage v.s. Junction Temperature**



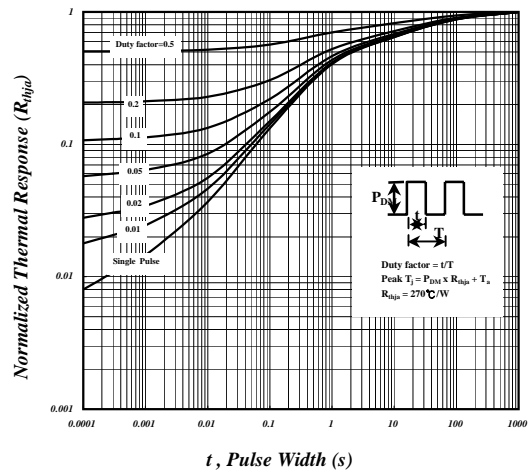
**Fig 7. Gate Charge Characteristics**



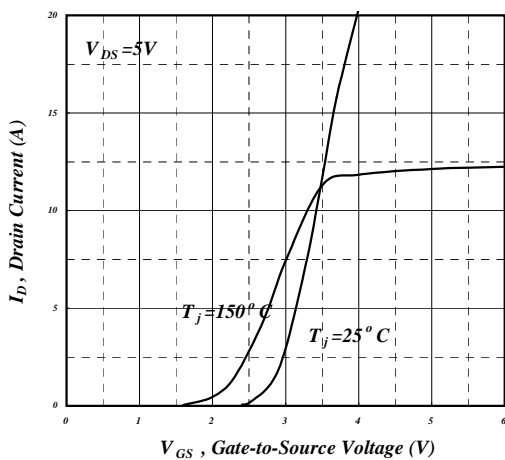
**Fig 8. Typical Capacitance Characteristics**



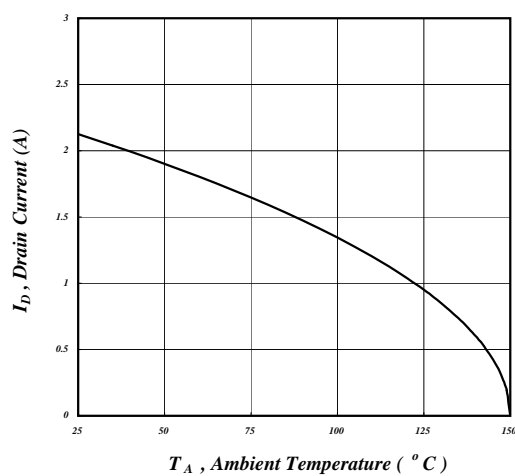
**Fig 9. Maximum Safe Operating Area**



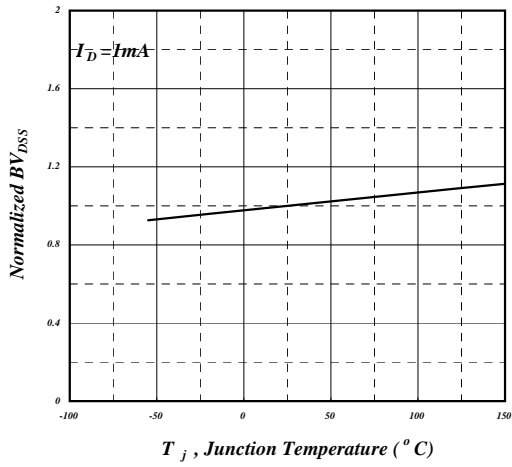
**Fig 10. Effective Transient Thermal Impedance**



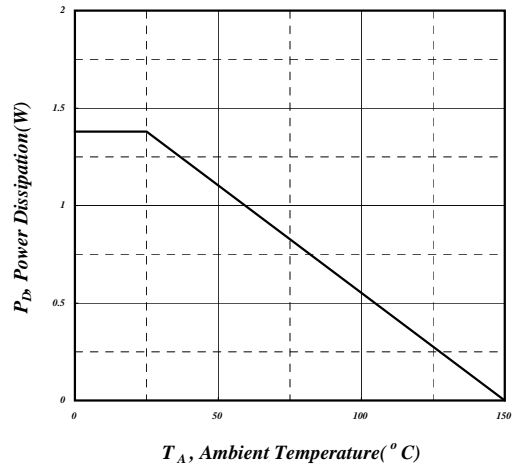
**Fig 11. Transfer Characteristics**



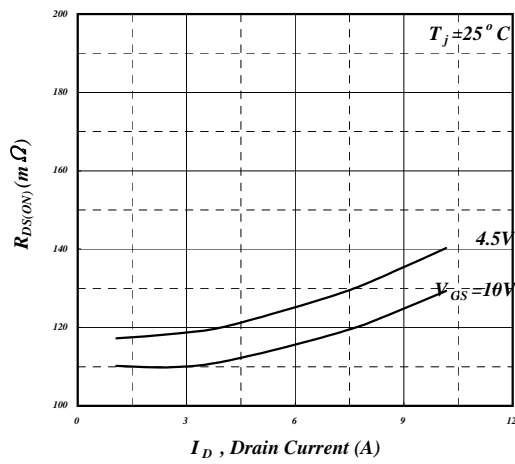
**Fig 12. Drain Current v.s. Ambient Temperature**



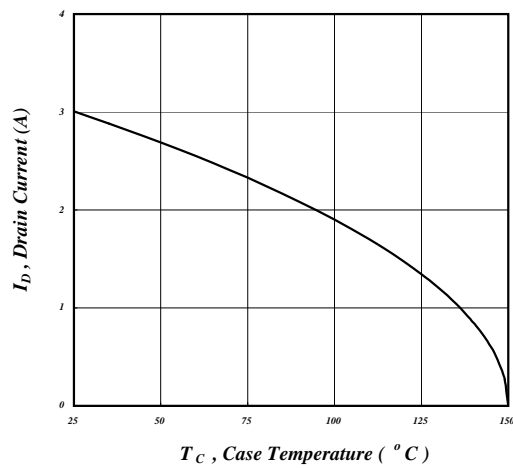
**Fig 13. Normalized  $BV_{DSS}$  v.s. Junction Temperature**



**Fig 14. Total Power Dissipation**

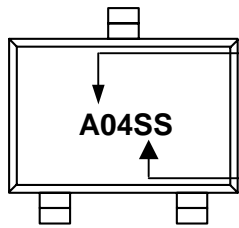


**Fig 15. Typ. Drain-Source on State Resistance**



**Fig 16. Drain Current v.s. Case Temperature**

## MARKING INFORMATION



Part Number : A04

Date Code : SS

SS:2004,2008,2012,2016,2020...

SS:2003,2007,2011,2015,2019...

SS:2002,2006,2010,2014,2018...

SS:2001,2005,2009,2013,2017...